

KTC3203 TRANSISTOR (NPN)

FEATURE

Power dissipation

P_{CM} : 0.625 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.8 A

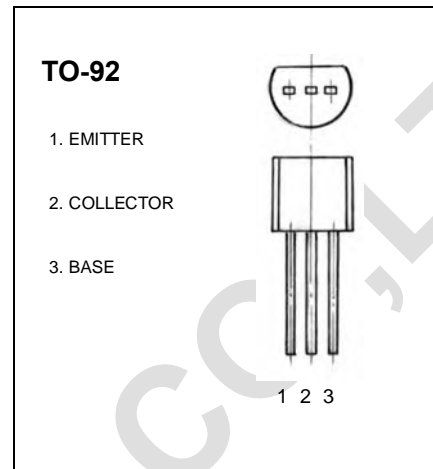
Collector-base voltage

$V_{(BR)CBO}$: 35 V

Operating and storage junction temperature range

T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

T_J : $150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{ mA}, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=35V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1V, I_C=100\text{mA}$	100		320	
	$h_{FE(2)}$	$V_{CE}=1V, I_C=700\text{mA}$	35			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{ mA}, I_B=20\text{mA}$			0.7	V
Base-emitter voltage	V_{BE}	$V_{CE}=1V, I_C=10\text{mA}$	0.5		0.8	V
Transition frequency	f_T	$V_{CE}=5\text{ V}, I_C=10\text{mA}$		120		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320